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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/586,675	07/20/2006	Ekkehard Mueh	288839US0PCT	8067	
OBLON, SPIVAK, MCCLELLAND MAIER & NEUSTADT, L.L.P. 1940 DUKE STREET			EXAMINER		
			MILLER, JR, JOSEPH ALBERT		
ALEXANDRIA, VA 22314			ART UNIT	PAPER NUMBER	
			1715		
			NOTIFICATION DATE	DELIVERY MODE	
			07/21/2011	ELECTRONIC	

# Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

Notice of the Office communication was sent electronically on above-indicated "Notification Date" to the following e-mail address(es):

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		Application No.	Applicant(s)			
Office Action Summary		10/586,675	MUEH ET AL.			
		Examiner	Art Unit			
		JOSEPH MILLER, JR	1715			
Period fo	The MAILING DATE of this communication apport	pears on the cover sheet with the c	orrespondence ad	idress		
WHIC - Exter after - If NC - Failu Any r	ORTENED STATUTORY PERIOD FOR REPLICHEVER IS LONGER, FROM THE MAILING Desions of time may be available under the provisions of 37 CFR 1.1 SIX (6) MONTHS from the mailing date of this communication. Period for reply is specified above, the maximum statutory period re to reply within the set or extended period for reply will, by statute reply received by the Office later than three months after the mailing and patent term adjustment. See 37 CFR 1.704(b).	ATE OF THIS COMMUNICATION 36(a). In no event, however, may a reply be time will apply and will expire SIX (6) MONTHS from a cause the application to become ABANDONE	N. nely filed the mailing date of this of D (35 U.S.C. § 133).			
Status						
1) 🛛	Responsive to communication(s) filed on <u>14 J</u>	iulv 2011.				
′=		s action is non-final.				
<i>'</i> —	, <del></del>		secution as to the	e merits is		
٥,۵	3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.					
	closed in accordance with the practice ander 1	expano adaylo, 1000 o.b. 11, 10	70 0.a. 210.			
Dispositi	on of Claims					
5) \[ \] 6) \[ \] 7) \[ \]	Claim(s) <u>1-8</u> is/are pending in the application.  4a) Of the above claim(s) <u>4 and 5</u> is/are withdr  Claim(s) is/are allowed.  Claim(s) <u>1-3 and 6-8</u> is/are rejected.  Claim(s) is/are objected to.  Claim(s) are subject to restriction and/or					
Applicati	on Papers					
10)	The specification is objected to by the Examine The drawing(s) filed on is/are: a) acc Applicant may not request that any objection to the Replacement drawing sheet(s) including the correct The oath or declaration is objected to by the Example 2.	epted or b) $\square$ objected to by the E drawing(s) be held in abeyance. See tion is required if the drawing(s) is obj	e 37 CFR 1.85(a). ected to. See 37 C	, ,		
Priority ι	ınder 35 U.S.C. § 119					
a)I	Acknowledgment is made of a claim for foreign All b) Some * c) None of:  1. Certified copies of the priority document 2. Certified copies of the priority document 3. Copies of the certified copies of the priority application from the International Burea See the attached detailed Office action for a list	ts have been received. ts have been received in Applicati rity documents have been receive u (PCT Rule 17.2(a)).	on No ed in this National	Stage		
Attachmen	t(s)					
	e of References Cited (PTO-892)	4) Interview Summary				
3) 🛛 Inform	e of Draftsperson's Patent Drawing Review (PTO-948) mation Disclosure Statement(s) (PTO/SB/08) r No(s)/Mail Date 05/14/2011_03/10/2011	Paper No(s)/Mail Da 5) Notice of Informal P 6) Other:				
C Detent and T	rademark Office					

### **DETAILED ACTION**

### Continued Examination Under 37 CFR 1.114

A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on 07/14/2011 has been entered.

## Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 1-3 and 6-8 are rejected under 35 U.S.C. 102(b) as being anticipated by O'Neill (2003/0049460), as further evidenced by RamachandraRao (2004/0072436).

O'Neill teaches the formation of a carbon containing SiO2-containing insulating layer [0015] whereby di-tert-butoxyacetoxysilane, an acetoxysilane, is applied on a semiconductor (i.e. "chip") substrate using CVD [0001, 0039-0044].

While O'Neill's film includes H and F as well as C [0016], O'Neill teaches that the in low k films (such as that produced by O'Neill's method), include incorporation of F

and C "into a SiO2 network" which effects the reduction in the dielectric constant [0009], therefore the teachings suggest that the produced film would be "SiO2-containing".

Because O'Neill's reference to the SiO2 network is in regard to the prior art, RamachandraRao is further evidenced in teaching that in low k dielectric films based on (silicon-based precursors) it is understood that materials are substituted into the SiO2 network. Based particularly on the high levels of O in the films of O'Neill [0016-17], one expects such an SiO2 network.

Regarding claim 2, as noted above, O'Neill teaches CVD.

Regarding claims 3 and 7, as noted, O'Neill teaches di-tert-butoxyacetoxysilane.

Regarding claims 6 and 8, the method is used to form a dielectric, i.e. insulating, layer on "chips" or semiconductor substrates as described, understood (particularly per claim 8) as a silicon wafer.

### Response to Arguments

Applicant's arguments with respect to instant claims have been considered but are most in view of the new ground(s) of rejection.

By cancelling out the species which the claims were previously rejected over, applicants have overcome the last rejections, as indicated in the Advisory Action mailed 06/24/2011. Examiner has further searched and found the new art, applied above, that teaches all claim elements.

Due to the large number of specific and groups of silicon compounds claimed, the scope of the search is still too broad for examiner to search ALL claimed

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compounds and groups. The deposition of SiO2-containing films is pervasive in the semiconductor art and the application of many different silicon compounds is known.

#### Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to JOSEPH MILLER JR whose telephone number is (571) 270-5825. The examiner is on a flexible schedule, but can normally be reached at least Mon - Thurs, 6am to 3:30pm. Other times as required are available for interviews.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Timothy Meeks, can be reached on 571-272-1423. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

/JOSEPH MILLER JR/ Examiner, Art Unit 1715